

**NPN Silicon RF power transistor**

**MRF323**

**Description:**

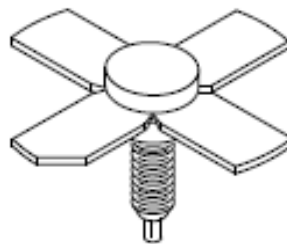
MRF323 is. designed primarily for wideband large–signal driver and predriver amplifier stages in the 200–500 MHz frequency range.

Guaranteed Performance at 400 MHz, 28 V  
 Output Power = 20 Watts  
 Power Gain = 10 dB Min  
 Efficiency = 50% Min

**MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V <sub>CEO</sub>	33	Vdc
Collector–Base Voltage	V <sub>CBO</sub>	60	Vdc
Emitter–Base Voltage	V <sub>EBO</sub>	4.0	Vdc
Collector Current — Continuous — Peak	I <sub>C</sub>	2.2 3.0	Adc
Total Device Dissipation @ T <sub>C</sub> = 25°C (1) Derate above 25°C	P <sub>D</sub>	55 310	Watts mW/°C
Storage Temperature Range	T <sub>stg</sub>	–65 to +150	°C

**Drawings:**



**SOT122/ CASE 244**